



Form 1449 (Modified)	Atty Docket No. UNTYP017	Application No.: 10/612,263
Information Disclosure Statement By Applicant	Applicant: Rinerson et al.	
(Use Several Sheets if Necessary)	Filing Date July 1, 2003	Group 2818

U.S. Patent Documents

Examiner Initial	No.	Patent No.	Date	Patentee	Class	Sub-class	Filing Date
<i>DN</i>	A	6,204,139	2001-03-20	Liu et al.			
	B	5,920,500	1999-07-06	Tehrani et al.			
	C	6,545,891	2003-04-08	Tringali et al.			
	D	6,504,753	2003-01-07	Scheuerlein et al.			
	E	6,483,736	2002-11-19	Johnson et al.			
	F	6,385,074	2002-05-07	Johnson et al.			
	G	6,351,406	2002-02-26	Johnson et al.			
	H	6,185,122	2001-02-06	Johnson et al.			
	I	6,034,882	2000-03-07	Johnson et al.			
	J	5,835,396	1998-11-10	Zhang			
<i>DN</i>	K	4,442,507	1994-04-10	Roesner			

U.S. Published Patent Applications

Examiner Initial	No.	Document No.	Publication Date	Inventor
<i>DN</i>	J	2002/0000597 A1	01/03/02	Okazawa
<i>DN</i>	K	2001/0023992 A1	09/27/01	Doll

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>DN</i>	L	Beck, A. et al., "Reproducible switching effect in thin oxide films for memory applications", Applied Physics Letters, Vol. 77, No. 1, 3 July 2000, 139-141.
	M	Rossel, C. et al., "Electrical current distribution across a metal-insulator-metal structure during bistable switching", Journal of Applied Physics, Vol. 90, No. 6, 15 September 2001, 2892-2898.
<i>DN</i>	N	Watanabe, Y. et al., "Current-driven insulator-conductor transition and nonvolatile memory in chromium-doped SrTiO ₃ single crystals", Applied Physics Letters, Vol. 78, No. 23, 4 June 2001, 3738-3740.
Examiner	TUAN T. NGUYEN	
	Date Considered	2/7/05

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.



Form 1449 (Modified) Information Disclosure Statement By Applicant (Use Several Sheets if Necessary)	Atty Docket No. UNTYP017 Applicant: Rinerson et al. Filing Date July 1, 2003	Application No.: 10/612,263 Group 2824
--	---	---

Other Documents

Examiner Initial	No.	Author, Title, Date, Place (e.g. Journal) of Publication
<i>De</i>	A	Liu, S.Q., et al., "Electric-pulse-induced reversible resistance change effect in magnetoresistive films", Applied Physics Letters, Vol. 76, No. 19, 8 May 2000, 2749-2651.
<i>De</i>	B	Liu, S.Q., et al., "A New Concept For Non-Volatile Memory: Electric-Pulse Induced Reversible Resistance Change Effect In Magnetoresistive Films", Space Vacuum Epitaxy Center, University of Huston, Huston TX, 7 Pages.
Examiner	Date Considered	
<i>TUAN T. NGUYEN</i>	<i>2/7/05</i>	

Examiner: Initial citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.